Development Plasma-based Atomic Layer Etching of Zinc Oxide by Using Tetrafluoromethane Plasma and Dimethylaluminum Chloride

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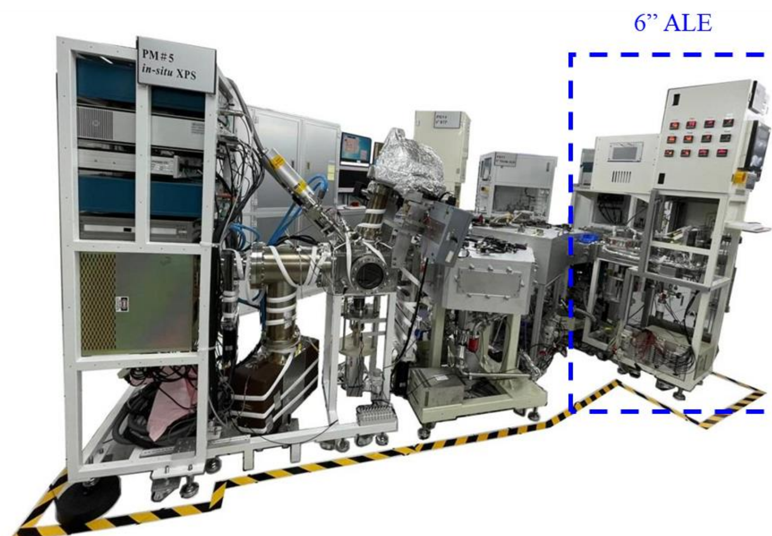

Figure 1. 6'' cluster ALE system developed by TIRI

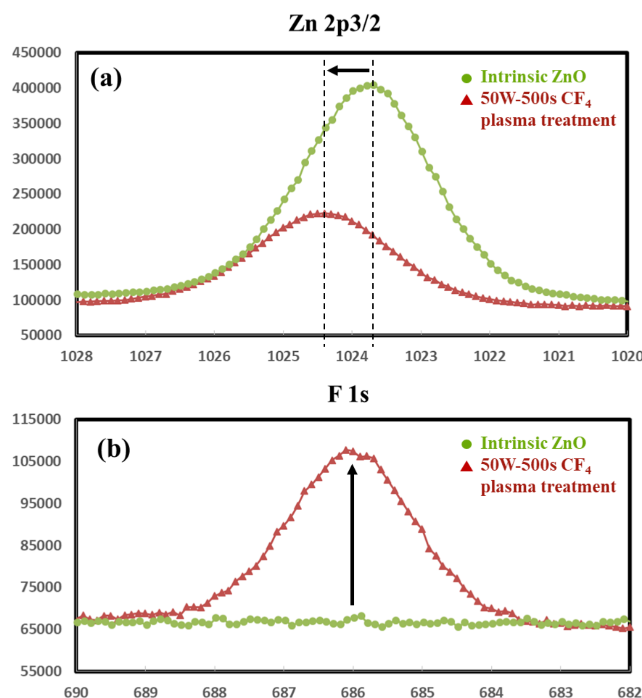

Figure 2. XPS spectra (Al anode) of (a) Zn 3/2p and (b) F 1s of ZnO treated by 50 W-10 s CF_4 plasma for 50 cycles at 0.5 Torr

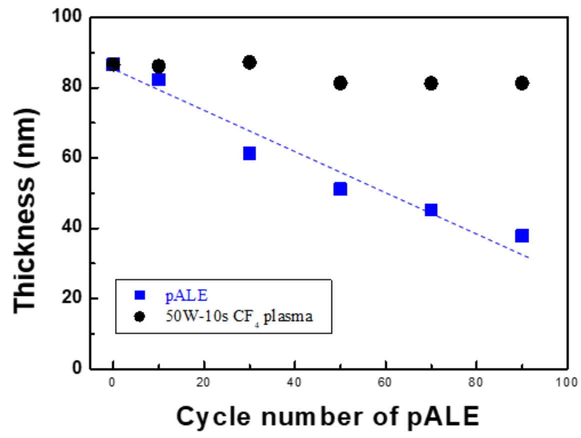

Figure 3. ZnO film thickness vs cycle number of pALE at 400℃